

MK eMMC Product Family

eMMC 5.1 Specification

Product List

MKEMF016GT1E-C / MKEMF032GT1E-C MKEMF064GT1E-C / MKEMF128GT2E-C

http://www.mkfounder.com



Revision History

Version	Version Date Descript	
Rev 1.0	2021/02/01	Released
Rev 1.1	2021/07/14	Modify CID value

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1 General Description

MK Founder e-MMC is an embedded flash memory storage solution.

MK Founder e·MMC is a hybrid device combining an embedded flash controller include LDPC based ECC and flash memory, with JEDEC Standard e·MMC 5.1 interface.

The e·MMC controller include LDPC based ECC directs the Flash management, including ECC, wear-leveling, IOPS optimization and read sensing, significantly reducing the storage management burden of the host CPU.

e·MMC is an ideal storage solution for many electronics devices. e·MMC designed to cover a wide area of application such as smart phones, Tablet PCs, Mobile phones, PDAs, Handheld electronics, Digital video cameras, Multimedia equipment, etc. Not only used in consumer products, e·MMC is being adopted rapidly in embedded applications, such as many Computer on Module designs, because of its compact size, low power consumption and many enhanced feature.

The technology specifications of e-MMC are managed by JEDEC, the global leader in developing open standards for the microelectronics industry.

2 Product List

Part Number	Density	PackageType	Package size	Remark
MKEMF016GT1E-C	16GB	FBGA153	11.5x13x1.0 (mm)	1 stack
MKEMF032GT1E-C	32GB	FBGA153	11.5x13x1.0 (mm)	1 stack
MKEMF064GT1E-C	64GB	FBGA153	11.5x13x1.0 (mm)	1 stack
MKEMF128GT2E-C	128GB	FBGA153	11.5x13x1.0 (mm)	2 stack

3 Key Features

- Support JEDEC/ e•MMC 5.1 Compliant
- Support 3.3V/1.8V power supply
- Support 12 wire bus (CLK, CMD, Data Strobe, DAT[7:0] and hardware reset (RST_n))
- Up to 400MHz clock speed
- Support Single Data Rate(SDR) and Dual Data Rate(DDR)
- Support different Bus width: 1bit, 4bit, 8bit
- Support Original Boot and Alternative Boot modes
- Support Data Removal (Erase, Trim and Sanitize)
- Support Replay Protected Memory Block(RPMB)



- Support Multiple Partitions with enhanced attribute
- Support Lock/Unlock and Write Protection
- Support Data Protection for Power Failure
- Support Power Saving Sleep Mode
- Support High Priority Interrupt(HPI)
- Support Background Operation
- Support Packed Commands
- Support Sampling Tuning Sequence
- Support Dynamic Power Manager : standby and sleep modes
- Support Command Queuing
- Support Secure Write Protection
- Package size
 - 11.5mm x 13.0mm x 1.0mm
- Operating Voltage range
 - $Vcc = 2.7V \sim 3.6V$ (typical 3.3V)
 - Vccq = 1.7V~1.95V(typical 1.8V), 2.7V~3.6V (typical 3.3V)
- Temperature
 - Operating : -25°C ~ 85°C
 - Storage : -40°C ~ 85°C



4 Functional Block Diagram

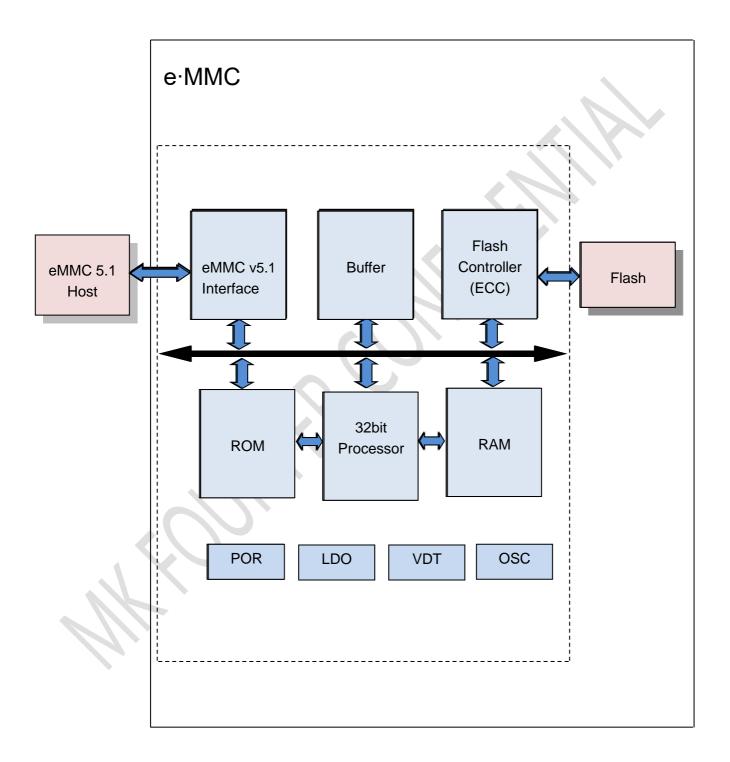


Figure 1 - e-MMC Block Diagram



5 e·MMC Device and System

5.1 e·MMC System Overview

The e·MMC specification covers the behavior of the interface and the device controller include LDPC based ECC. AS part of this specification the existence of a host controller include LDPC based ECC and a memory storage array are implied but the operation of these pieces is not fully specified

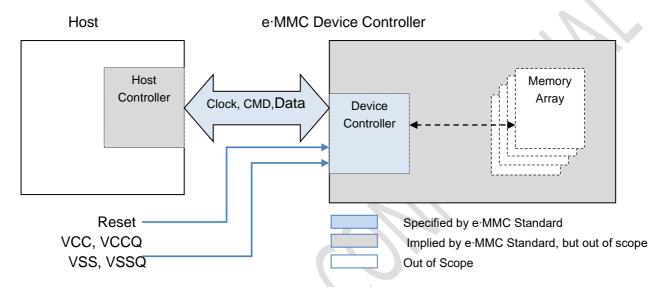


Figure 2 - e-MMC System Overview

5.2 e·MMC Device Overview

The e-MMC bus has the following communication and power lines

- CLK : Clock Input
- DS: Data strobe used for output in HS400 mode.
- CMD : Command is a bidirectional signal. The host and e⋅MMC operate in two modes, open drain and push-pull
- DAT0~DAT7: Data lines are bidirectional signal. Host and e·MMC operate in push-pull mode.
- RST_n : Hardware Reset Input
- VCC: VCC is the power supply for core and flash IO.
- VCCQ: VCCQ is the power supply line for host interface
- VSS, VSSQ : Ground lines.



Name	Туре	Description				
CLK	1	Clock				
DS	O/PP	Data Strobe				
DAT0	I/O/PP	Data				
DAT1	I/O/PP	Data				
DAT2	I/O/PP	Data				
DAT3	I/O/PP	Data				
DAT4	I/O/PP	Data				
DAT5	I/O/PP	Data				
DAT6	I/O/PP	Data				
DAT7	I/O/PP	Data				
CMD	I/O/PP/OD	Command/Response				
RST_n	1	Hardware reset				
VCC	S	Supply voltage for Core				
VCCQ	S	Supply voltage for I/O				
VSS	S	Supply voltage ground for Core				
VSSQ	S	Supply voltage ground for I/O				
I: input, O: output, PP: push-pull, OD: open-drain, NC: Not connected, S: power supply						

Table 1 e-MMC Interface

Name	Width (bytes)	Description	Implementation
CID	16	Device Identification number, an individual number for Identification.	Mandatory
RCA	2	Relative Device Address, is the device system address, Dynamically assigned by the host during initialization.	Mandatory
DSR	2	Driver stage Resister, to configure the Device's output drivers.	Optional
CSD	16	Device Specific Data, information about the Device operation Conditions.	Mandatory
OCR	4	Operation Conditions Resister. Used by a special broadcast command to identify the voltage type of the Device.	Mandatory
EXT_CSD	512	Extended Device Specific Data. Contains information about the Device capabilities and selected modes. Introduced in standard v4.0	Mandatory

Table 2 e-MMC registers



6 e·MMC 5.1 Feature Overview

6.1 Boot

e·MMC supports JESD84-B51A boot operation mode, both mandatory as well as alternate mode are supported.

6.2 Sleep (CMD5)

A Device may be switched between a Sleep state and a Standby state by SLEEP/AWAK(CMD5). In the Sleep State the power consumption of the memory device is minimized. In this state the memory device reacts only to the commands RESET(CMD0 with argument of either 0x00000000 or 0XF0F0F-0f0 or H/W reset) and SLEEP/AWAKE(CMD5). All the other commands are ignored by the memory device.

The Vcc power supply may be switched off in Sleep state is to enable even further system power con-sumption saving.

For additional information please refer JESD84-B51A.

6.3 Bus Modes

Boot mode

The device will be in boot mode after power cycle, reception of CMD0 with argument of 0xF0F0F0F0 or the assertion of hardware reset signal.

Device identification mode

The device will be in device identification mode after boot operation mode is finished or if host and/or device does not support boot operation mode. The device will be in this mode, until the SET_RCA command (CMD3) is received.

Interrupt mode

Host and device enter and exit interrupt mode simultaneously. In interrupt mode there is no data transfer.

The only message allowed is an interrupt service request from the device or the host.



Data transfer mode

The device will enter data transfer mode once an RCA is assigned to it. The host will enter data transfer

mode after identifying the device on the bus

Inactive mode

The device will enter inactive mode if either the device operating voltage range or access mode is not valid.

The device can also enter inactive mode with GO_INACTIVE_STATE command(CMD15). The device will reset to Pre-idle state with power cycle.

Device State	Operation mode	Bus mode
Inactive State	Inactive mode	
Pre-Idle State	Boot mode	
Pre-Boot State	Boot mode	Open drain
Idle State		Open-drain
Identification State	Device identification mode	
Stand-by State		
Sleep State		Push-pull
Transfer State		·
Bus-Test State		
Sending-data State	Data transfer mode	
Receive-data State		
Programming State		
Disconnect State		
Boot State	Boot mode	
Wait-IRQ State	Interrupt mode	Open-drain

Table 3 Bus mode's overview



6.4 Reliable Write

e·MMC supports 512Bytes reliable write as defined in e·MMC 5.1 spec.

Reliable write is a special write mode in which the old data pointed to by a logical address must remain unchanged until the new data written to same logical address has been successfully programmed.

This is to ensure that the target address updated by the reliable write transaction never contains undefined data. When writing reliable write, data will remain valid even if a sudden power loss occurs during programming.

6.5 Secure Erase

In addition to the standard Erase command the e·MMC support the optional Secure erase command. The Secure Erase command differs from the basic Erase command in that it requires the device and host to wait until the operation is complete before moving to the next device operation.

For additional information please refer JESD84-B51A.

The secure erase command requires device to perform a secure purge operation on the erase groups, and copy items identified for erase, in those erase groups.

A purge operation is defined as overwriting addressable location with a single character and the performing an erase.

This new command meets high security application requirements that once data has been erased, it can no longer be retrieved from device.

6.6 Secure Trim

The Secure Trim command is very similar to the Secure Erase command. The Secure Trim command performs a secure purge operation on write blocks instead of erase groups. To minimize the impact on the device's performance and reliability the Secure Trim operation is completed by executing two distinct steps.



6.7 Trim

The Trim function is similar to the Erase command but applies the erase operation to write blocks instead of erase groups.

For additional information please refer JESD84-B51A.

6.8 Partition Management

The default area of the memory device consists of a User Data Area to store data, two possible boot area partitions for booting and the Replay Protected Memory Block Area Partition to manage data in an authenticated and replay protected manner. The memory configuration initially consists(before any partitioning operation) of the User Data Area and RPMB Area Partitions and Boot Area Partitions.

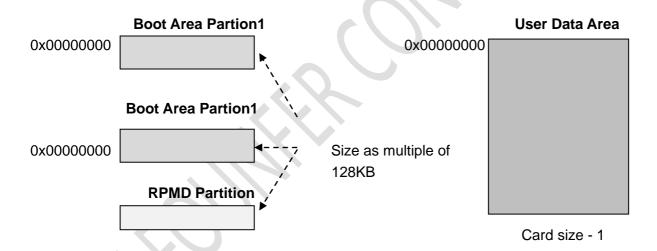


Figure 3 e-MMC memory organization at time zero



6.9 High priority interrupt (HPI)

Many operating systems use demand-paging to launch a process requested by the user. If the host needs to fetch pages while in a middle of a wire operation, the request will be delayed until the completion of the write command which, in the worst case scenario, can take up to 350ms.

The high priority interrupt (HPI) as defined in JESD84-B51A enables low read latency operation by suspending a lower priority operation before it is actually completed. This mechanism can reduce read latency, in typical condition, to 5msec

For additional information please refer JESD84-B51A.

6.10 Background Operations

Devices have various maintenance operations that they need to perform internally, such as garbage collection, erase and compaction. In order to reduce latencies during time critical operations, it is better to execute maintenance operations when the device is not serving the host.

Operations are then separated into two types: foreground operations – such as read or write command, and background operations- operations that the device can execute when the host is not being served.

For additional information please refer JESD84-B51A.

6.11 H/W Reset

Hardware reset may be used by host to reset the device, moving the card to a Pre-Idle state and disabling the power-on period write protect on blocks that was set as power-on write protect before the reset was asserted.

For additional information please refer JESD84-B51A.

6.12 Packed Commands

Read and write commands can be packed in groups of commands (either all read or all write) that transfer the data for all commands in the group in one transfer on the bus to reduce overheads.



6.13 Cache

Cache is temporary storage space in an e·MMC device. The cache should in typical case reduce the access time (compared to an access to the main non-voltage) for both write and read. The cache is not directly accessible by the host. This temporary storage space may be utilized also for some implementation specific operations like as an execution memory for the memory controller include LDPC based ECC and/or as storage for an address mapping table etc but which definition is out of scope of this specification.

For additional information please refer JESD84-B51A.

6.14 Discard

The Discard is similar operation to TRIM. The Discard function allows the host to identify data that is no longer required so that the device can erase the data if necessary during background erase events. The contents of a write block where the discard function has been applied shall be 'don't care'. After discard operation, the original data may be remained partially or fully accessible to the host dependent on device. The portions of data that are no longer accessible by the host may be removed or unmapped just as in the case of TRIM. The device will decide the contents of discarded write block.

For additional information please refer JESD84-B51A.

6.15 Sanitize

The sanitize operation is a feature, in addition to TRIM and Erase that is used to remove data from the device. The use of the Sanitize operation requires the device to physically remove data from the unmapped user address space. A Sanitize operation is initiated by writing a value to the extended CSD[165] SANITIZE_START.



6.16 Dynamic Capacity Management

Extensive memory usage and aging of Flash could result in bad block.

Dynamic Capacity Management provides a mechanism for the memory device to reduce its reported capacity and extend the device life time.

The mechanism to manipulate dynamic capacity is based on: memory array partitioning and the granularity of WP groups. Reducing the capacity is done by releasing of WP-groups anywhere within the address space of the user area. A released WP-Group will behave as a permanently write protected group and it shall not be read from: Writing to an address within a released WP-Group returns a WP error; Reading form an address tithing a released WP-Group is forbidden and may return an error; Checking write protection (using CMD30) and write protect type (using CMD31) shall report protected groups and permanent write protection accordingly.

For additional information please refer JESD84-B51A.

7 Product Specifications

7.1 Power Consumption

Power Consumption	16GB	32GB	64GB	128GB	Units
Standby(VCCQ & VCC on)	130	130	140	150	uA
Sleep (VCCQ on, VCC off)	130	130	140	140	uA
HS400 Read VCC	35	35	40	40	mA
HS400 Read VCCQ	120	120	120	125	mA
HS400 Write VCC	50	50	50	55	mA
HS400 Write VCCQ	70	70	65	65	mA

Table 4 Power Consumption (Ta=25°C @VCC=3.3V & VCCQ=1.8V)



7.2 Performance

HS400 Performance	16GB	32GB	64GB	128GB	Units
Sequential Read	210	210	210	295	MB/s
Sequential Write	170	170	170	190	MB/s
Random Read	4000	4000	4000	8000	IOPS
Random Write	4300	4300	4300	7000	IOPS

Table 5 Performance

7.3 Operating Conditions

	Temperature	Remark
Operating	-25°C ~ 85°C	
Non-Operating	-40°C ~ 85°C	

Table 6 Operating and Storage Temperature



7.4 Physical Specification

e·MMC is a 153pin, thin fine-pitched ball grid array.(BGA)

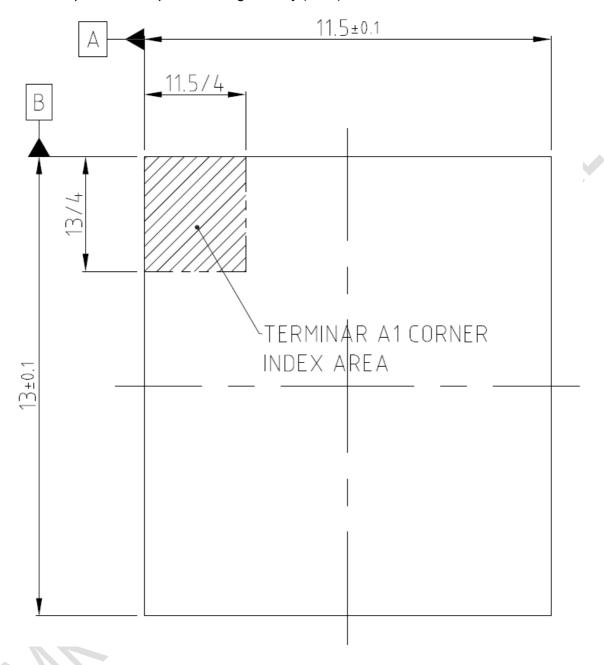


Figure 4 11.5 x 13.0 x 1.0mm Top View



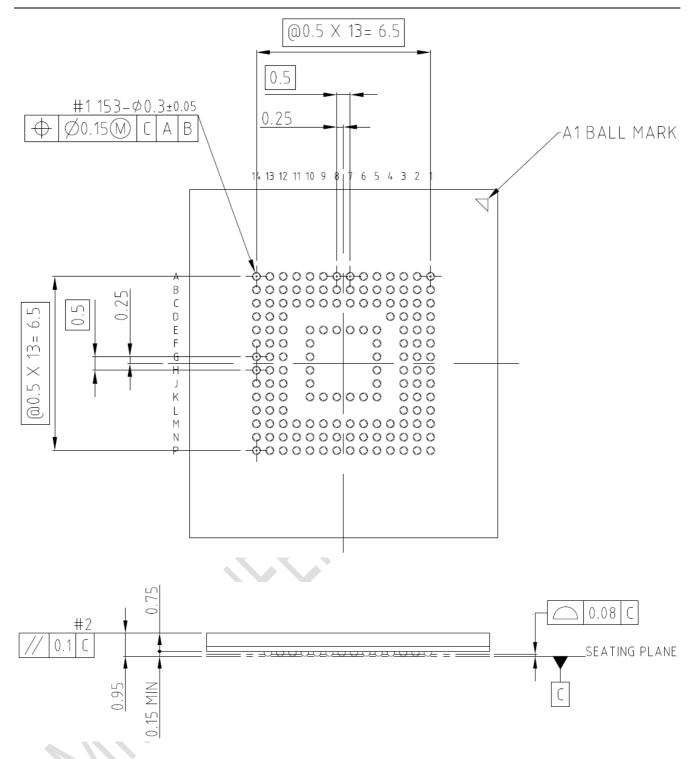


Figure 5 11.5 x 13.0 x 1.0mm Bottom & side View



8 Interface Description

8.1 e·MMC Interface ball array

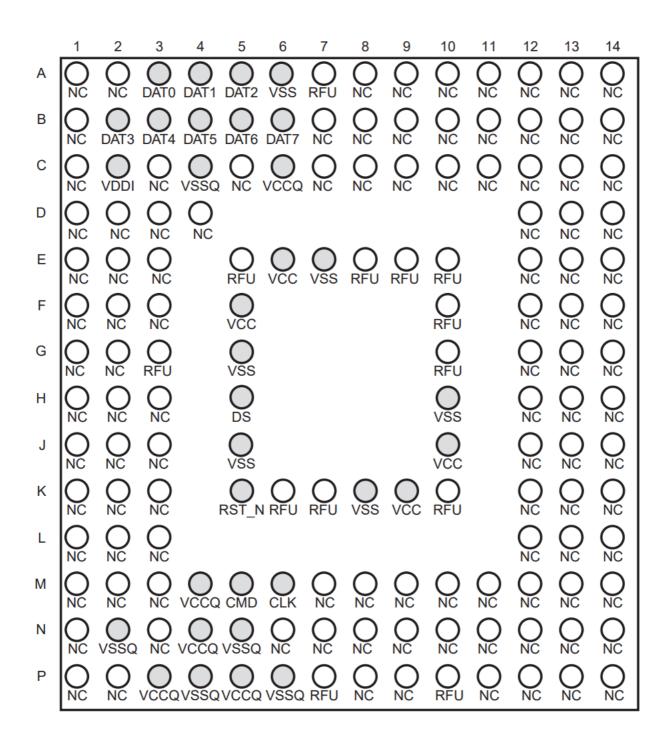


Figure 6 FBGA153 Package Connection (top view through package)



8.2 Pins and Signal Description

153-Ball Device	Symbol	Туре	Ball Function
M6	CLK	Input	Clock: Each cycle directs a 1-bit transfer on the com-mand and DAT lines.
M5	CMD	Input	Command: A bidirectional channel used for device initiali-zation and command transfer. Command has two operating mode: 1) Open-drain for initialization. 2) Push-pull for fast command transfer.
А3	DAT0	I/O	Data I/O0: Bidirectional channel used for data transfer.
A4	DAT1	I/O	Data I/O1: Bidirectional channel used for data transfer.
A5	DAT2	I/O	Data I/O2: Bidirectional channel used for data transfer.
B2	DAT3	I/O	Data I/O3: Bidirectional channel used for data transfer.
В3	DAT4	I/O	Data I/O4: Bidirectional channel used for data transfer.
B4	DAT5	I/O	Data I/O5: Bidirectional channel used for data transfer.
B5	DAT6	I/O	Data I/O6: Bidirectional channel used for data transfer.
В6	DAT7	1/0	Data I/O7: Bidirectional channel used for data transfer.
K5	RST_n	Input	Reset signal pin
E6, F5, J10, K9	VCC	Supply	VCC: Flash memory I/F and Flash memory power supply.
C6, M4, N4, P3, P5	VccQ	Supply	VccQ: Memory controller core and MMC interface I/O power supply.
E7, G5, H10, K8	VSS	Supply	Vss: Flash memory I/F and Flash memory ground connection.
C4, N2, N5, P4, P6	VssQ	Supply	VssQ
C2	VDDi		VDDi : Connect 1uF capacitor from VDDi to ground.
H5	DS		Data Strobe : Return clock signal used in HS400 mode

Table 7 Pin and signal Description



9 Device Resisters

9.1 Operating Condition Resister (OCR)

The 32-bit operation condition register(OCR) store the Vdd voltage profile of the e·MMC and the access mode indication. In addition, this register includes a status information bit. This status bit is set if the e·MMC power up procedure has been finished. The OCR register shall be implemented by e·MMC.

OCR bit	Description	Value	Remark			
[6:0]	Reserved	000 0000b				
[7]	1.70 ~ 1.95V	1b				
[14:8]	2.0 ~ 2.6V	000 0000b				
[23:15]	2.7 ~ 3.6V	1 1111 1111b				
[28:24]	Reserved	0 0000b				
[30:29]	Access mode	10b				
[31]	card power up status bit (busy)1					

¹⁾This bit is set to LOW if the Device has not finished the power up routine.

Table 8 OCR register definition

9.2 Card Identification Resister (CID)

The Card Identification(CID) register is 128 bits wide. In contains the Device identification information used during the Device identification phase(e·MMC protocol). Every individual flash or I/O Device shall have an unique identification number. Table 21 lists these identifiers.

The structure of the CID register is defined in the following section.

Name	Field	Width	CID-Slice	CID Value	Remark
Manufacture ID	MID	8	[127:120]	F2h	
Reserved		6	[119:114]		
Card / BGA	CBX	2	[113:112]	01h	BGA
OEM/Application ID	OID	8	[111:104]	FFh	Not fixed
			[103:56]	MK016D (16GB)	
Product name	PNM	48		MK032D (32GB)	Not fixed
				MK064D (64GB)	
				MK128D (128GB)	
Product revision	PRV	8	[55:48]	FFh	Not fixed
Product serial number	PSN 32	PSN 32 [47:16]	[47:16]	Random by	Not fixed
Froduct Serial Humber			[47.10]	Production	NOT IIXEU
Manufacturing date	MDT	8	[15:8]	month, year	Not fixed
CRC7 checksum	CRC	7	[7:1]	0h	Not fixed
Not used, always '1'	-	1	[0:0]	0h	



Table 9 Card Identification register definition

9.3 Card Specific Data Resister (CSD)

The Device-specific Data (CSD) register provides information on how to access the Device contents. The CSD defines the data format, error correction type, maximum data access time, data transfer speed, whether the DSR register can be used etc. The programmable part of the register(entries marked by W or E, see below) can be changed by CMD27. The type of the CSD Registry entries below is coded as follows:

- R: Read only
- W : One time programmable and not readable.
- R/W : One time programmable and readable
- W/E: Multiple writable with value kept after power failure, H/W reset assertion and any CMD0 reset and not readable.
- R/W/E: Multiple writable with value kept after power failure, H/W reset assertion and any CMD0 reset and not readable.
- R/W/C_P: Writeable after value cleared by power failure and H/W reset assertion (the value not cleared by CMD0 reset) and readable.
- R/W/E_P: Multiple writable with value reset after power failure, H/W reset assertion and any CMD0 reset and readable.
- W/E_P: Multiple writable with value reset power failure, H/W reset assertion and any CMD0 reset and not readable.

Name	Field	Width	Cell type	CSD Slice	CSD Value	Remark			
CSD structure	CSD_STRUCTURE	2	R	[127:126]	3h				
System Specification version	SPEC_VERS	4	R	[125:122]	4h				
Reserved	-	2	R	[121:120]					
Data read access-time 1	TAAC	8	R	[119:112]	2Fh	20ms			
Data read access-time 2in CLK cycle (NSAC*100)	NSAC	8	R	[111:104]	1h				
Max. bus clock frequency	TRAN_SPEED	8	R	[103:96]	2Ah	20MHz			
Device command classes	CCC	12	R	[95:84]	5F5 h	Class 0,2,4,5,6 ,7,8,10			
Max. read data block length	READ_BL_LEN	4	R	[83:80]	9h	512B			
Partial blocks for read allowed	READ_BL_PARTIAL	1	R	[79:79]	0h	Not support			
Write block misalignment	WIRTE_BLK_MISALIG N	1	R	[78:78]	0h	Not support			
Name	Field	Width	Cell	CSD	CSD Value	Remark			



			type	Slice		
Read block misalignment	READ_BLK_MISALIGN	1	R	[77:77]	0h	Not support
DSR implemented	DSR_IMP	1	R	[76:76]	0h	Not support
Reserved	_	2	R	[75:74]		
Device size	C_SIZE	12	R	[73:62]	FFF h	
Max read current @VDD min	VDD_R_CURR_MIN	3	R	[61:59]	6h	
Max read current @VDD max	VDD_R_CURR_MAX	3	R	[58:56]	6h	
Max write current @VDD min	VDD_W_CURR_MIN	3	R	[53:53]	6h	
Max write current @VDD max	VDD_W_CURR_MAX	3	R	[52:50]	6h	
Device size multiplier	C_SIZE_MULT	3	R	[49:47]	7h	
Erase group size	ERASE_GRP_SIZE	5	R	[46:42]	1Fh	
Erase group size multiplier	ERASE_GRP_MULT	5	R	[41:37]	1Fh	
Write protect group size	WP_GRP_SIZE		R	[36:32]	1Fh	
Write protect group enable	enable WP_GRP_ENABLE		R	[31:31]	1h	
Manufacturer default ECC	DEFAULT_ECC	2	R	[30:29]	0h	
Write speed factor	R2W_FACTOR	3	R	[28:26]	1h	
Max. write data block length	WRITE_BL_LEN	4	R	[25:22]	9h	512B
Partial blocks for write allowed	WRITE_BL_PARTIAL	1	R	[21:21]	0h	Not support
Reserved		4	R	[20:17]		
Content protection application	CONTENT_PROT_AP P	1	R	[16:16]	0h	Not support
File format group	FILE_FORMAT_GRP	1	R/W	[15:15]	0h	
Copy flag (OTP)	COPY	1	R/W	[14:14]	0h	
Permanent write protection	PERM_WRITE_PROTE CT	1	R/W	[13:13]	0h	
Temporary write protection	TMP_WRITE_PROTEC T	1	R/W/ E	[12:12]	0h	
File format	FILE_FORMAT		R/W	[11:10]	0h	
ECC code	ECC code ECC		R/W/ E	[9:8]	0h	None
CRC	CRC	7	R/W/ E	[7:1]	7h	
Not used, always' 1'		1	-	[0:0]	1h	

The following sections describe the CSD fields and the relevant data types. If not explicitly defined otherwise, all bit strings are interpreted as binary coded numbers starting with the left bit first.



Table 10 CSD Field

9.4 Extended CSD Resister

The Extended CSD register defines the Device properties and selected modes. It is 512bytes long. The most significant 320bytes are the Properties segment, which defines the Device capabilities and cannot be modified by the host. The lower 192bytes are the Modes segment, which defines the configuration the Device is working in. These modes can be changed by the host means of the SWITCH command.

For details, refer to section 7.4 of the JEDEC Standard Specification No. JESD84-B51A.

	I				
Name	Field	Cell type	CSD Slice	EXT_CS D Value	Remark
Properties Segment					
Reserved₁	RESERVED	TBD	[511:5 06]		
Extended Security Command Error	EXT_SECURITY_ER R	R	[505]	0h	Only for eMMC4.5 by JESD84-B51A
Supported Command Sets	S_CMD_SET	R	[504]	1h	Allocated by MMCA
					Bit[1]=1: HPI mechanism implementation base on CMD12
HPI features	HPI_FEATURES	R	[503]	3h	Bit[1]=0: HPI mechanism implementation base on CMD13
	Men.				Bit[0]=1: HPI mechanism support Bit[0]=0: HPI mechanism not support
					(default)
Background operations support	BKOPS_SUPPORT	R	[502]	1h	Background operation are supported
Max packed read commands	MAX_PACKED_REA DS	R	[501]	5h	
Max packed write commands	MAX_PACKED_WRI TES	R	[500]	3h	
Data Tag Support	DATA_TAG_SUPPO RT	R	[499]	1h	System data tag supported
Tag Unit Size	TAG_UNIT_SIZE	R	[498]	1h	1024Bytes
Tag Resources Size	TAG_RES_SIZE	R	[497]	0h	
Context Management Capabilities	CONTEXT_CAPABIL ITIES	R	[496]	5h	
Large Unit Size	LARGE_UNIT_SIZE _M1	R	[495]	0h	
Extended partition Attribute Support	EXT_SUPPORT	R	[494]	3h	



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Supported modes	SUPPORTED_MOD ES	R	[493]	1h	
FFU features	FFU_FEATURES	R	[492]	1h	
Operation codes timeout	OPERATION_CODE _TIMEOUT	R	[491]	17h	
FFU Argument	FFU_ARG	R	[490:4 87]	0h	
Barrier support	BARRIER_SUPPOR T	R	[486]	0h	
Reserved1		TBD	[485:3 09]		
CMD Queuing Support	CMDQ_SUPPORT	R	[308]	0h	
CMD Queuing Depth	CMDQ_DEPTH	R	[307]	0h	
Reserved1		TBD	[306]		
Number of FW sectors correctly programmed	NUMBER_OF_FW_ SECTORS_CORRE CTLY_PROGRAMM ED	R	[305:3 02]	0h	
Vendor proprietary health report	VENDOR_PROPRIE TARY_HEALTH_RE PORT	R	[301:2 70]	0h	
Device life time estimation type B	DEVICE_LIFE_TIME _EST_TYP_B	R	[269]	1h	
Device life time estimation type A	DEVICE_LIFE_TIME _EST_TYP_A	R	[268]	1h	
Pre EOL information	PRE_EOL_INFO	R	[267]	1h	
Optimal read size	OPTIMAL_READ_SI ZE	R	[266]	8h	
Optimal write size	OPTIMAL_WRITE_S IZE	R	[265]	8h	
Optimal trim unit size	OPTIMAL_TRIM_UN IT_SIZE	R	[264]	8h	
Device version	DEVICE_VERSION	R	[263:2 62]	0h	
Firmware version	FIRMWARE_VERSI ON	R	[261:2 54]		
Power class for 200MHz, DDR at VCC= 3.6V	PWR_CL_DDR_200 _360	R	[253]	0h	
Cache size	CACHE_SIZE	R	[252:2 49]	80h	
Generic CMD6 timeout	GENERIC_CMD5_TI ME	R	[248]	32h	
Name	Field	Cell type	CSD Slice	EXT_CS D Value	Remark
Power off notification (long)timeout	POWER_OFF_LON G_TIME	R	[247]	3Ch	
Background operations status	BKOPS_STATUS	R	[246]	0h	Outstanding : No operation required
	1		L		



Number of correctly SECTORS_NUM R 245:2 Oh						
Description Cache Flushing Policy Cache Flushing	=		R	-	0h	
Power class for 52MHz, DR at VCC = 3.6V PWR_CL_DDR_52_ 360 R [239] Oh DR at VCC = 3.6V Power class for 52MHz, DR at VCC = 1.95V, Power class for 52MHz, 195 R [237] Oh R		INI_TIMEOUT_AP	R	[241]	1Eh	Initial time out 3s
DDR at VCC = 3.6V 360	Cache Flushing Policy		R	[240]	0h	
DDR at VCC = 1-95V	*		R	[239]	0h	
Act CCQ = 1.95V, VCC = 3.6V	,		R	[238]	0h	
At VCCQ = 1.3V, VCC = 3.6V PWR_CL_200_130 R [236] Oh	at VCCQ = 1.95V, VCC =	PWR_CL_200_195	R	[237]	0h	
Performance for 8bit At 52MHz in DDR mode Minimum Read Performance for 8bit At 52MHz in DDR mode Reservedt Reservedt RESERVED RESER	at VCCQ = 1.3V, VCC = 3.6V	PWR_CL_200_130	R	[236]	0h	
Performance for 8bit At 52MHz in DDR mode Reserved: RESERVED TBD [233] TRIM Multiplier TRIM_MULT R [232] 2h TRIM Timeout =300ms*2=600ms 1. Support the sanitize operation 2. Support the secure and insecure trim operation 3. Support the auto erase on retired defective portion of array 4. Secure purge operations are supported defective portion of array 4. Secure Erase Timeout= 5.1 sec Secure TRIM Multiplier SEC_TRIM_MULT R [230] 1Bh Secure trim Timeout= 8.1 sec Secure TRIM Multiplier BOOT_INFO R [228] 7h Bit[0]=1: Device supports high speed timing during boot Bit[1]=1: Device supports alternate boot method Bit[0]=1: Device supports alte	Performance for 8bit At 52MHz in DDR mode		R	[235]	0h	
TRIM Multiplier TRIM_MULT R [232] 2h TRIM Timeout =300ms*2=600ms 1. Support the sanitize operation 2. Support the secure and insecure trim operation 3. Support the auto erase on retired defective portion of array 4. Secure purge operations are supported Secure TRIM Multiplier SEC_ERASE_MULT R [230] Secure Erase Timeout= 5.1 sec Secure trim Timeout= 8.1 sec Bit[2]=1: Device supports high speed timing during boot Bit[0]=1: Device supports alternate boot method Bit[0]=1: Device supports during boot Bit[0]=1: Device supports during boot Bit[0]=1: Device supports during boot Bit[0]=1: Device supports duri	Performance for 8bit		R	[234]	0h	
Secure Feature support SEC_FEATURE_SU PPORT R [231] 55h 2. Support the sanitize operation 2. Support the secure and insecure trim operation 3. Support the auto erase on retired defective portion of array 4. Secure purge operations are supported Secure Erase Multiplier SEC_ERASE_MULT R [230] 1Bh Secure Erase Timeout= 5.1 sec Secure trim Timeout= 8.1 sec Bit[2]=1: Device supports high speed timing during boot Bit[1]=1: Device supports dual data rate during boot Bit[0]=1: Device supports alternate boot method Bit[0,1,2]=0: Not supports each feature Bit[7:3=Reserved Reserved: Reserve	Reserved₁	RESERVED	TBD	[233]		
Secure Feature support SEC_FEATURE_SU PPORT R [231] 55h 2. Support the secure and insecure trim operation 3. Support the auto erase on retired defective portion of array 4. Secure purge operations are supported Secure Erase Multiplier SEC_ERASE_MULT R [230] 1Bh Secure Erase Timeout= 5.1 sec Secure TRIM Multiplier SEC_TRIM_MULT R [229] 11h Secure trim Timeout= 8.1 sec Bit[2]=1: Device supports high speed timing during boot Bit[1]=1: Device supports dual data rate during boot Bit[0]=1: Device supports alternate boot method Bit[0]=1: Device su	TRIM Multiplier	TRIM_MULT	R	[232]	2h	TRIM Timeout =300ms*2=600ms
Secure Erase Multiplier SEC_ERASE_MULT R [230] 1Bh 5.1 sec Secure TRIM Multiplier SEC_TRIM_MULT R [229] 11h Secure trim Timeout= 8.1 sec Bit[2]=1: Device supports high speed timing during boot Bit[1]=1: Device supports dual data rate during boot Bit[0]=1: Device supports alternate boot method Bit[0,1,2]=0: Not supports each feature Bit[7:3=Reserved] Reserved	Secure Feature support		R	[231]	55h	Support the secure and insecure trim operation Support the auto erase on retired defective portion of array
Boot information BOOT_INFO R [228] 11h 8.1 sec Bit[2]=1: Device supports high speed timing during boot Bit[1]=1: Device supports dual data rate during boot Bit[0]=1: Device supports alternate boot method Bit[0,1,2]=0: Not supports each feature Bit[7:3=Reserved Reserved1 RESERVED TBD [227] Boot partition size Bit[2]=1: Device supports high speed timing during boot Bit[0]=1: Device supports alternate boot method Bit[0,1,2]=0: Not supports each feature Bit[7:3=Reserved Remark 227]	Secure Erase Multiplier	SEC_ERASE_MULT	R	[230]	1Bh	
Boot information BOOT_INFO R [228] 7h Sit[1]=1: Device supports dual data rate during boot	Secure TRIM Multiplier	SEC_TRIM_MULT	R	[229]	11h	
Name Field Cell type Slice D value Remark Reserved1 RESERVED TBD [227] Boot partition size BOOT_SIZE_MULT R [226] 20h	Boot information	BOOT_INFO	R			timing during boot Bit[1]=1: Device supports dual data rate during boot Bit[0]=1: Device supports alternate boot method Bit[0,1,2]=0: Not supports each feature
Boot partition size BOOT_SIZE_MULT R [226] 20h	Name	Field			D	Remark
	Reserved₁	RESERVED	TBD	[227]		
Access size ACC_SIZE R [225] 1h	Boot partition size	BOOT_SIZE_MULT	R	[226]	20h	
	Access size	ACC_SIZE	R	[225]	1h	



High-capacity erase unit size	HC_ERASE_GRP_S IZE	R	[224]	1h	
High-capacity erase timeout	ERASE_TIMEOUT_ MULT	R	[223]	20h	
Reliable write sector count	REL_WR_SEC_C	R	[222]	1h	1sector
High-capacity write protect group size	HC_WP_GRP_SIZE	R	[221]	20h	
Sleep current (VCC)	S_C_VCC	R	[220]	7h	Sleep Current :128uA
Sleep current(VCCQ)	s_c_vccq	R	[219]	7h	Sleep Current :128uA
Production state awareness timeout	PRODUCTION_STA TE_AWARENESS_T IMEOUT	R	[218]	17h	
Sleep/awake timeout	S_A_TIMEOUT	R	[217]	17h	Sleep/Awake Timeout : 85ms
Sleep Notification Timeout	SLEEP_NOTIFICATI ON_TIME	R	[216]	11h	
Sector Count	SEC_COUNT	R	[215:2 12]		73A000h
Secure Write Protect Information	SECURE_WP_INFO	TBD	[211]	0h	
Minimum Write Performance for 8bit At 52MHz	MIN_PERF_W_8_52	R	[210]	0h	
Minimum Read Performance for 8bit At 52MHz	MIN_PERF_R_8_52	R	[209]	0h	
Minimum Write Performance for 8bit at 26MHz, for 4bit at 52MHz	MIN_PERF_W_8_26 _4_52	R	[208]	0h	
Minimum Write Performance for 8bit at 26MHz, for 4bit at 52MHz	MIN_PERF_R_8_26 _4_52	R	[207]	0h	
Minimum Write Performance for 4bit at 26MHz	MIN_PERF_W_4_26	R	[206]	0h	
Minimum Write Performance for 4bit at 26MHz	MIN_PERF_R_26	R	[205]	0h	
Reserved ₁	RESERVED	R	[204]		
Power class for 26MHz at 3.6V 1R	PWR_CL_26_360	R	[203]	0h	MAX RMS Current = 100mA, MAX Peak Current = 200mA
Power class for 52MHz at 3.6V 1R	PWR_CL_52_360	R	[202]	0h	MAX RMS Current = 100mA, MAX Peak Current = 200mA
Name	Field	Cell type	CSD Slice	EXT_CS D Value	Remark
Power class for 26MHz at 1.95V 1R	PWR_CL_26_195	R	[201]	0h	MAX RMS Current = 65mA, MAX Peak Current = 130mA
Power class for 52MHz at 1.95V 1R	PWR_CL_52_195	R	[200]	0h	MAX RMS Current = 65mA, MAX Peak Current = 130mA
Partition switching timing	PARTITION_SWITC H_TIME	R	[199]	5h	Partition switch time : 10ms



timing	OUT_OF_INTERRU PT_TIME	R	[198]	19h	LIDI (
river Strength			[.00]	1311	HPI time out : 20ms
	DRIVER_STRENGT H	R	[197]	Fh	Support driver strength: Type0,1,2,3
evice type	DEVICE_TYPE	R	[196]	57h	1. HS400 @1.8V 2. High-speed Data Rate 52@1.8V/3.3V 3. High-speed Data Rate 52@rated device voltage(s) 4. High-speed Data Rate 26@rated device voltage(s)
Reserved1	RESERVED	TBD	[195]		
SD structure C	CSD_STRUCTURE	R	[194]	2h	CSD version No.1.2
Reserved ₁	RESERVED	TBD	[193]		
d CSD revision	EXT_CSD_REV	R	[192]	8h	Revision 1.8(for MMC v5.1)
des Segment					
command set	CMD_SET	R/W/E_ P	[191]	0h	
Reserved ₁	RESERVED	TBD	[190]		
and set revision	CMD_SET_REV	R	[189]	0h	V4.0
Reserved ₁	RESERVED	TBD	[188]		
ower class	POWER_CLASS	R/W/E_ P	[187]	0h	See EXT_CSD in spec.
Reserved ₁	RESERVED	TBD	[186]		
speed interface timing	HS_TIMING	R/W/E_ P	[185]	0h	It depends on Host I/F speed. Default is 0, But it can be 1 by host
obe Support S	STROBE_SUPPORT	R	[184]	1h	
width mode	BUS_WIDTH	W/E_P	[183]	0h	
Reserved ₁	RESERVED		[182]		
memory content	ERASED_MEM_CO NT	R	[181]	0h	0 after erase
Name	Field	Cell type	CSD Slice	EXT_CS D Value	Remark
Reserved ₁	RESERVED	TBD	[180]		
on configuration F	PARTITION_CONFI G	R/W/E & R/W /E_P	[179]	0h	
ontig protection	BOOT_CONFIG_PR OT	R/W/E & R/W /C_P	[178]	0h	
ous Conditions B	BOOT_BUS_CONDI TIONS	R/W/E	[177]	0h	
des Segment Command set Reserved1 and set revision Reserved1 ower class Reserved1 speed interface timing obe Support width mode Reserved1 memory content Name Reserved1 on configuration B	CMD_SET RESERVED CMD_SET_REV RESERVED POWER_CLASS RESERVED HS_TIMING STROBE_SUPPORT BUS_WIDTH RESERVED ERASED_MEM_CO NT Field RESERVED PARTITION_CONFI G BOOT_CONFIG_PR OT BOOT_BUS_CONDI	R/W/E_P TBD R/W/E_P TBD R/W/E_P R R R W/E_P R R R R R R R R R R R R R R R R R R R	[192] [191] [190] [189] [188] [187] [186] [185] [184] [183] [182] [181] CSD Slice [180] [179]	Oh O	V4.0 See EXT_CSD in spec. It depends on Host I/F speed. Defau But it can be 1 by host 0 after erase



Reserved ₁	RESERVED	TBD	[176]		
High-density erase group definition	ERASE_GROUP_D EF	R	[175]	0h	
Boot write protection status registers		TBD	[174]	0h	
Boot area write protection register	BOOT_WP	R/W/E & R/W /C_P	[173]	0h	Bit[6]=0 : Master is permitted to set B_PWR_WP_EN (bit0) Bit[4]=0 : Master is permitted to set B_PERM_WP_EN (bit2) Bit[2]=0 : Boot Region is not permanently write protected Bit[0]=0 : Boot Region is not power-on write protected
Reserved ₁	RESERVED	TBD	[172]		
User area write protection register	USER_WP	R/W, & R/W /C_P & RW /E_P	[171]	0h	
Reserved1	RESERVED	TBD	[170]		
FW configuration	FW_CONFIG	R/W	[169]	0h	FW updates enabled
RPMB Size	RPMB_SIZE_MULT	R	[168]	20h	RPMB size 4096KB
Write reliability setting register	WR_REL_SET	R/W	[167]	0h	
Write reliability parameter register	WR_REL_PARAM	R	[166]	15h	Enhanced definition of reliable write 2. All the WR_DATA_REL parameter in the WR_REL_SEL register are R/W
Name	Field	Cell type	CSD Slice	EXT_CS D Value	Remark
Start Sanitize operation	SANITIZE_START	W/E_P	[165]	0h	
Manually start background operations	BKOPS_EN	W/E_P	[164]	0h	
Enable background operations handshake	BKOPS_EN	R/W	[163]	0h	
H/W reset function	RST_n_FUNCTION	R/W	[162]	0h	
HPI management	HPI_MGMT	R/W/E_ P	[161]	0h	
Partitioning Support	PARTITIONING_SU PPORT	R	[160]	7h	Can have extended partitions attribute Can have enhanced technological features 3. Device supports partitioning features



		1			
Max Enhanced Area Size	MAX_ENH_SIZE_M ULT	R	[159:1 57]		73A000h
Partitions attribute	PARTITIONS_ATTR UBUTE	R/W	[156]	Oh	Bit[7:5]: Reserved Bit[4]=1: Set Enhanced attribute in General Purpose partition 4 Bit[3]=1: Set Enhanced attribute in General Purpose partition 3 Bit[2]=1: Set Enhanced attribute in
					General Purpose partition 2 Bit[1]=1: Set Enhanced attribute in General Purpose partition 1
Partitioning Setting	PARTITON_SETTIN G_ COMPLETED	R/W	[155]	0h	
General Purpose Partition Size	GP_SIZE_MULT	R/W	[154:1 43]	0h	
Enhanced User Data Area Size	ENH_SIZE_MULT	R/W	[142:1 40]	0h	
Enhanced User Data Start Address	ENH_START_ADDR	R/W	[139:1 36]	0h	
Reserved ₁	RESERVED	TBD	[135]		
Bad Block Management mode	SEC_BAD_BLK_MG MNT	R/W	[134]	0h	
Production state awareness	PRODUCTION_STATE _AWARENESS	R/W/E	[133]	0h	
Name	Field	Cell type	CSD Slice	EXT_CS D Value	Remark
Package Case Temperature is Controlled	TCASE_SUPPORT	W/E_P	[132]	0h	
Periodic Wake-up	PERIODIC_WAKEU P	R/W/E	[131]	0h	
Program CID/CSD in DDR mode Support	PROGRAM_CID_CS D_DDR_SUPPORT	R	[130]	1h	
Reserved ₁	RESERVED	TBD	[129:1 28]		
Vendor Specific Fields	VENDOR_SPECIFIC _FIELD		[127:6 4]	0h	
Native sector size	NATIVE_SECTOR_S IZE	R	[63]	0h	
Sector size emulation	USE_NATIVE_SECT OR	R/W	[62]	0h	
Sector size 1st initialization after	DATA_SECTOR_SIZ E	R	[61]	0h	
disabling sector size emulation	INI_TIMEOUT_EMU	R	[60]	0h	
Class 6 commands control	CLASS_6_CTRL	R/W/E_ P	[59]	0h	



Number of addressed group to be Released	DYNCAP_NEEDED	R	[58]	0h				
Exception event control	EXCEPTION_EVEN TS_CTRL	R/W/E_ P	[57:56]	0h				
Exception event status	EXCEPTION_EVEN TS_STATUS	R	[55:54]	0h				
Extended Partitions Attribute	EXT_PARTITIONS_ ATTRIBUTE	R/W	[53:52]	0h				
Context configuration	CONTEXT_CONF	R/W/E_ P	[51:37]	0h				
Packed command status	PACKED_COMMAN D_STATUS	R	[36]	0h				
Packed command failure index	PACKED_FAILURE_ INDEX	R	[35]	0h				
Power Off Notification	POWER_OFF_NOTI FICATION	R/W/E_ P	[34]	0h	Power off notification is not supported by host, device should not assume any notification			
Control to turn the Cache ON/OFF	CACHE_CTRL	R/W/E_ P	[33]	0h				
Flushing of the cache	FLUSH_CACHE	W/E_P	[32]	0h				
Control to turn the Barrier ON/OFF	BARRIER_CTRL	R/W	[31]	0h				
Mode config	MODE_CONFIG	R/W/E_ P	[30]	0h				
Mode operation codes	MODE_OPERATION _CODES	W/E_P	[29]	0h				
Reserved1		TBD	[28:27					
FFU status	FFU_STATUS	R	[26]	0h				
Pre loading data size	PRE_LOADING_DAT A_SIZE	R/W/E_ P	[25:22	0h				
Max pre loading data size	MAX_PRE_LOADIN G_DATA_SIZE	R	[21:18		73A000h			
Product state awareness enablement	PRODUCT_STATE_ AWARENESS_ENA BLEMENT	R/W/E &	[17]	3h				
Secure Removal Type	SECURE_REMOVA L_TYPE	R/W/E &	[16]	9h				
Command Queue Mode Enable	CMDQ_MODE_EN	R/W/E_ P	[15]	0h				
Reserved1		TBD	[14:0]					
NOTE1. Reserved bits should read as "0" NOTE2. Obsolete values should be don't care								

Table 11 Extended CSD Field